

Silicon NPN Power Transistors

2SC2761

DESCRIPTION

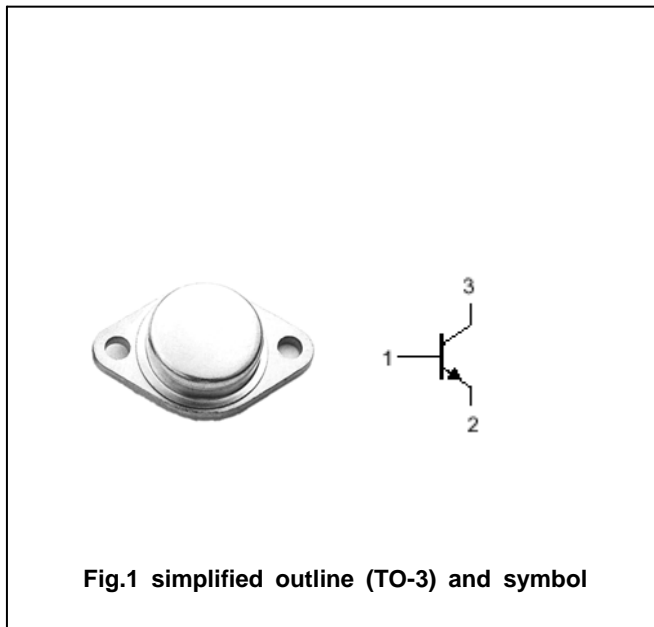
- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor controls

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	450	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		30	A
I_B	Base current		6	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	200	W
T_j	Junction temperature		200	°C
T_{stg}	Storage temperature		-65~200	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0	400			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1m A ; I _E =0	450			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1m A ; I _C =0	7			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =20A; I _B =4A			1.5	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =20A; I _B =4A			1.7	V
I _{CBO}	Collector cut-off current	V _{CB} =450V I _E =0			100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			100	μ A
h _{FE}	DC current gain	I _C =15A ; V _{CE} =2V	8			

PACKAGE OUTLINE

